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MMBT2222ALT1 is a Preferred Device

General Purpose Transistors

NPN Silicon

Features

• Pb-Free Packages are Available

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage MMBT2222LT1 MMBT2222ALT1	V _{CEO}	30 40	Vdc
Collector - Base Voltage MMBT2222LT1 MMBT2222ALT1	V _{CBO}	60 75	Vdc
Emitter - Base Voltage MMBT2222LT1 MMBT2222ALT1	V _{EBO}	5.0 6.0	Vdc
Collector Current - Continuous	Ic	600	mAdc
Collector Current - Peak (Note 3)	I _{CM}	1100	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) T _A = 25°C Derate above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate (Note 2) T _A = 25°C Derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

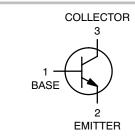
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

- 1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = 0.4 \times 0.3 \times 0.024 in. 99.5% alumina.
- 3. Reference SOA curve.



ON Semiconductor®

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SOT-23 CASE 318 STYLE 6

MARKING DIAGRAM



xxx = 1P or M1B
M = Date Code*
• = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector - Emitter Breakdown Voltage (I _C = 10 mAdc, I _B = 0) MMBT2222A	MMBT2222	V _{(BR)CEO}	30 40		Vdc
Collector – Base Breakdown Voltage ($I_C = 10 \mu Adc, I_E = 0$) MMBT2222A	MMBT2222	V _{(BR)CBO}	60 75	- -	Vdc
Emitter – Base Breakdown Voltage (I_E = 10 μ Adc, I_C = 0) MMBT2222A	MMBT2222	V _{(BR)EBO}	5.0 6.0		Vdc
Collector Cutoff Current (V _{CE} = 60 Vdc, V _{EB(off)} = 3.0 Vdc)	MMBT2222A	I _{CEX}	-	10	nAdc
	MMBT2222 MMBT2222A MMBT2222 MMBT2222A	I _{CBO}	- - -	0.01 0.01 10 10	μAdc
Emitter Cutoff Current ($V_{EB} = 3.0 \text{ Vdc}$, $I_{C} = 0$)	MMBT2222A	I _{EBO}	-	100	nAdc
Base Cutoff Current (V _{CE} = 60 Vdc, V _{EB(off)} = 3.0 Vdc)	MMBT2222A	I _{BL}	-	20	nAdc
ON CHARACTERISTICS					
DC Current Gain	MMBT2222A only MMBT2222 MMBT2222A	h _{FE}	35 50 75 35 100 50 30 40	- - - 300 - - -	-
Collector - Emitter Saturation Voltage (Note 4) (I _C = 150 mAdc, I _B = 15 mAdc)	MMBT2222 MMBT2222A	V _{CE(sat)}	- -	0.4 0.3	Vdc
$(I_C = 500 \text{ mAdc}, I_B = 50 \text{ mAdc})$	MMBT2222 MMBT2222A		-	1.6 1.0	
Base - Emitter Saturation Voltage (Note 4) (I _C = 150 mAdc, I _B = 15 mAdc)	MMBT2222 MMBT2222A	V _{BE(sat)}	_ 0.6	1.3 1.2	Vdc
$(I_C = 500 \text{ mAdc}, I_B = 50 \text{ mAdc})$	MMBT2222 MMBT2222A			2.6 2.0	
SMALL-SIGNAL CHARACTERISTICS		1		•	
Current - Gain - Bandwidth Product (Note 5) (I _C = 20 mAdc, V _{CE} = 20 Vdc, f = 100 MHz)	MMBT2222 MMBT2222A	f _T	250 300		MHz
Output Capacitance ($V_{CB} = 10 \text{ Vdc}$, $I_E = 0$, $f = 1.0 \text{ MHz}$)		C _{obo}	_	8.0	pF
Input Capacitance ($V_{EB} = 0.5 \text{ Vdc}$, $I_{C} = 0$, $f = 1.0 \text{ MHz}$)	MMBT2222 MMBT2222A	C _{ibo}	- -	30 25	pF
Input Impedance $ \begin{aligned} \text{(I}_{C} &= 1.0 \text{ mAdc, V}_{CE} = 10 \text{ Vdc, f} = 1.0 \text{ kHz)} \\ \text{(I}_{C} &= 10 \text{ mAdc, V}_{CE} = 10 \text{ Vdc, f} = 1.0 \text{ kHz)} \end{aligned} $	MMBT2222A MMBT2222A	h _{ie}	2.0 0.25	8.0 1.25	kΩ
Voltage Feedback Ratio $ \begin{array}{l} \text{(I}_{C} = 1.0 \text{ mAdc, V}_{CE} = 10 \text{ Vdc, f} = 1.0 \text{ kHz)} \\ \text{(I}_{C} = 10 \text{ mAdc, V}_{CE} = 10 \text{ Vdc, f} = 1.0 \text{ kHz)} \end{array} $	MMBT2222A MMBT2222A	h _{re}	- -	8.0 4.0	X 10 ⁻⁴
$\begin{aligned} & \text{Small-Signal Current Gain} \\ & \text{(I}_{\text{C}} = 1.0 \text{ mAdc, V}_{\text{CE}} = 10 \text{ Vdc, f} = 1.0 \text{ kHz)} \\ & \text{(I}_{\text{C}} = 10 \text{ mAdc, V}_{\text{CE}} = 10 \text{ Vdc, f} = 1.0 \text{ kHz)} \end{aligned}$	MMBT2222A MMBT2222A	h _{fe}	50 75	300 375	-
Output Admittance $ \begin{aligned} &(I_C=1.0 \text{ mAdc, } V_{CE}=10 \text{ Vdc, } f=1.0 \text{ kHz}) \\ &(I_C=10 \text{ mAdc, } V_{CE}=10 \text{ Vdc, } f=1.0 \text{ kHz}) \end{aligned} $	MMBT2222A MMBT2222A	h _{oe}	5.0 25	35 200	μmhos

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Charact	Symbol	Min	Max	Unit			
SMALL-SIGNAL CHARACTERISTICS							
Collector Base Time Constant (I _E = 20 mAdc, V _{CB} = 20 Vdc, f =	rb, C _c	-	150	ps			
Noise Figure (I _C = 100 μ Adc, V _{CE} = 10 Vdc, R _S	NF	-	4.0	dB			
SWITCHING CHARACTERISTICS (MMBT2222A only)							
Delay Time	(V _{CC} = 30 Vdc, V _{BE(off)} = -0.5 Vdc, I _C = 150 mAdc, I _{B1} = 15 mAdc)	t _d	-	10	no		
Rise Time	$I_C = 150 \text{ mAdc}, I_{B1} = 15 \text{ mAdc})$	t _r	-	25	ns		
Storage Time	(V _{CC} = 30 Vdc, I _C = 150 mAdc,	t _s	-	225	ns		
Fall Time	$I_{B1} = I_{B2} = 15 \text{ mAdc}$	t _f	_	60	115		

- 4. Pulse Test: Pulse Width $\leq 300 \ \mu s$, Duty Cycle $\leq 2.0\%$.
- 5. f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.

SWITCHING TIME EQUIVALENT TEST CIRCUITS

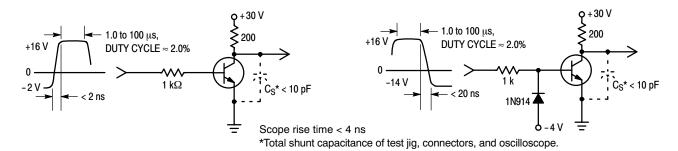


Figure 1. Turn-On Time

Figure 2. Turn-Off Time

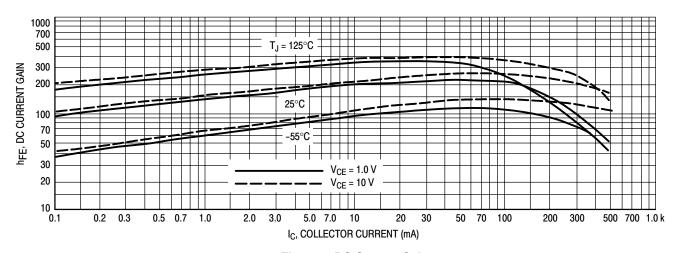


Figure 3. DC Current Gain

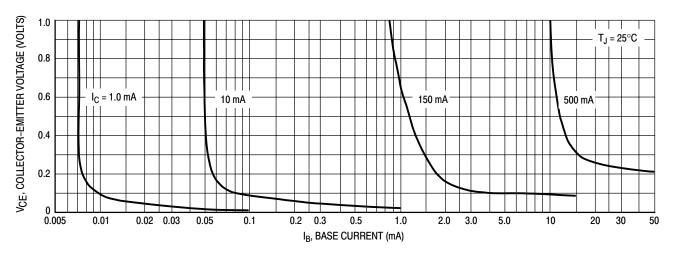


Figure 4. Collector Saturation Region

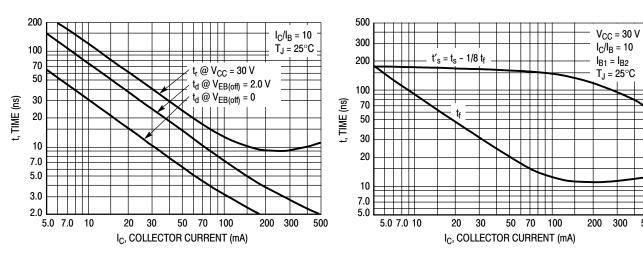


Figure 5. Turn-On Time

Figure 6. Turn-Off Time

500

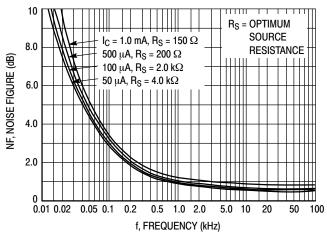


Figure 7. Frequency Effects

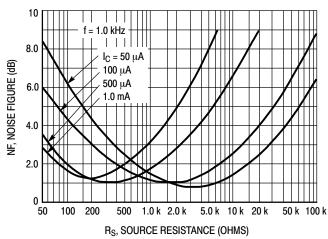
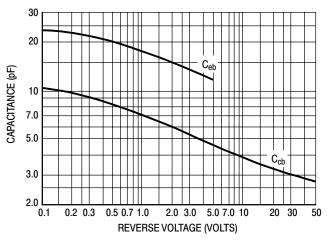


Figure 8. Source Resistance Effects



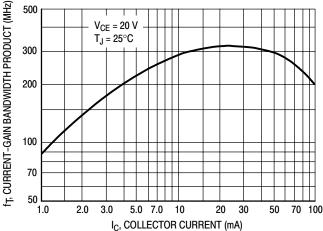
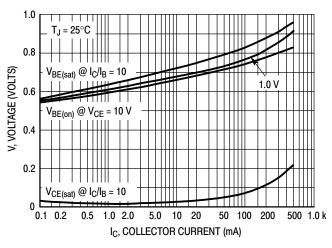


Figure 9. Capacitances

Figure 10. Current-Gain Bandwidth Product



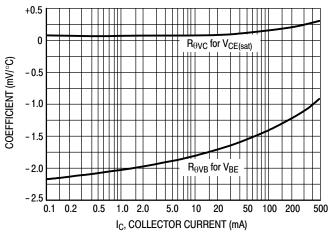


Figure 11. "On" Voltages

Figure 12. Temperature Coefficients

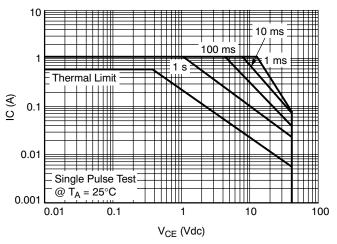


Figure 13. Safe Operating Area

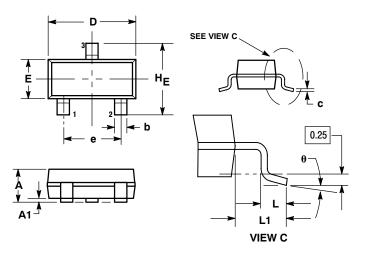
ORDERING INFORMATION

Device	Specific Marking Code	Package	Shipping [†]		
MMBT2222LT1	M1B	SOT-23	3000 / Tape & Reel		
MMBT2222LT1G	M1B	SOT-23 (Pb-Free)	3000 / Tape & Reel		
MMBT2222ALT1	1P	SOT-23	3000 / Tape & Reel		
MMBT2222ALT1G	1P	SOT-23 (Pb-Free)	3000 / Tape & Reel		
MMBT2222LT3	M1B	SOT-23	10,000 / Tape & Reel		
MMBT2222LT3G	M1B	SOT-23 (Pb-Free)	10,000 / Tape & Reel		
MMBT2222ALT3	1P	SOT-23	10,000 / Tape & Reel		
MMBT2222ALT3G	1P SOT-23 (Pb-Free)		10,000 / Tape & Reel		

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AN**



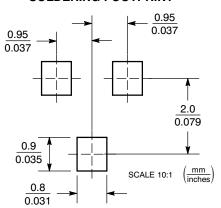
- DIMENSIONING AND TOLERANCING PER
- DIMENSIONING AND TOLEHANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: INCH.
 LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE
- BASE MATERIAL. 4. 318-01 THRU -07 AND -09 OBSOLETE, NEW STANDARD 318-08

	MILLIMETERS		INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
С	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104

STYLE 6: PIN 1. BASE

- **EMITTER**
- COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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